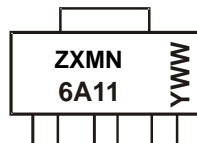


Marking Information

SOT223 (Type DN)



ZXMN6A11 = Product Type Marking Code
 YWW = Date Code Marking
 Y or \bar{Y} = Last Digit of Year (ex: 2= 2022)
 WW or $\bar{W}W$ = Week Code (01~53)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$ unless otherwise specified.)

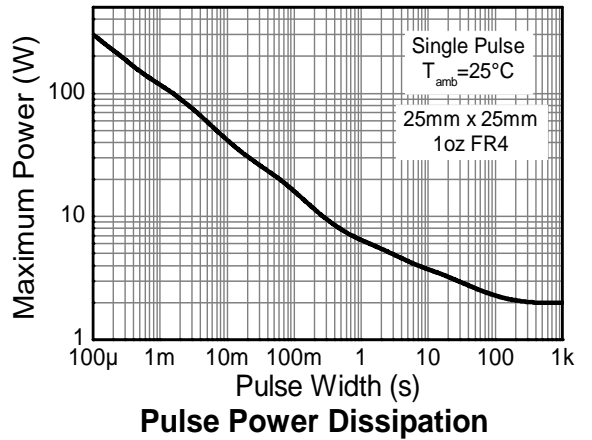
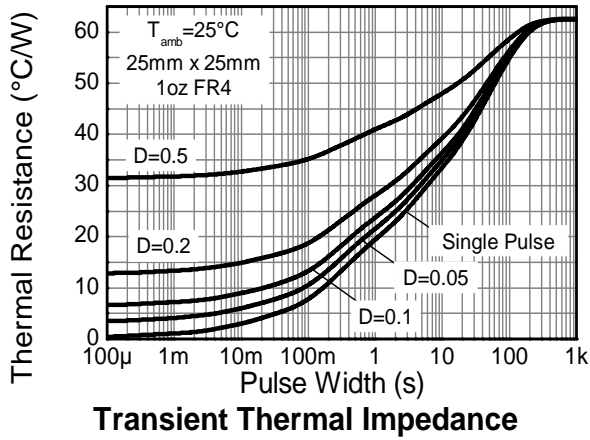
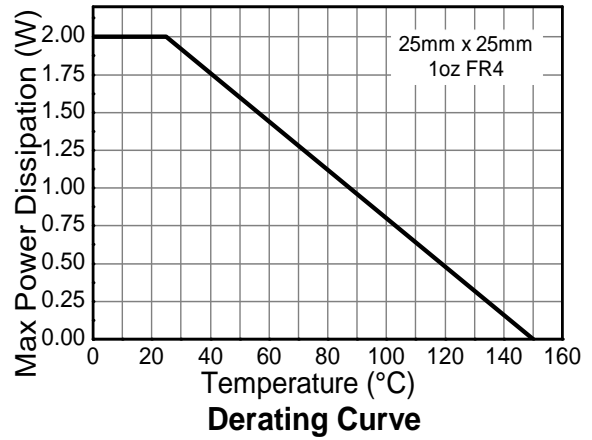
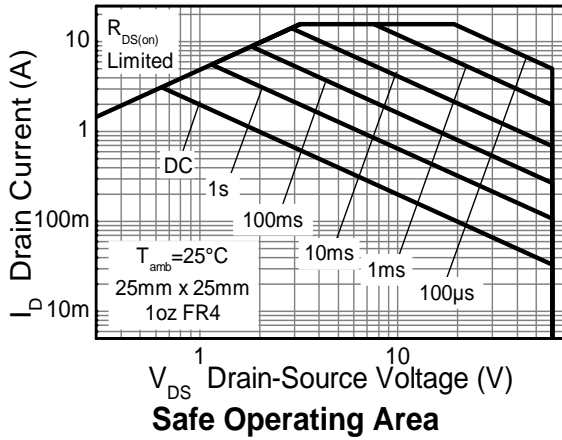
Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DS}	60	V
Gate-Source Voltage			V_{GS}	± 20	
Continuous Drain Current	$V_{GS} = 10\text{V}$	(Note 6)	I_D	4.4	A
		$T_A = +70^\circ\text{C}$ (Note 6)		3.5	
		(Note 5)		3.1	
Pulsed Drain Current	$V_{GS} = 10\text{V}$	(Note 7)	I_{DM}	15.6	
Continuous Source Current (Body Diode)			(Note 6)	I_S	
Pulsed Source Current (Body Diode)			(Note 7)	I_{SM}	15.6

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$ unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P_D	2.0	W
	Linear Derating Factor		16	
(Note 6)			3.9	
			31	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
	(Note 6)		32.0	
Thermal Resistance, Junction to Lead	(Note 8)	$R_{\theta JL}$	9.8	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	

- Notes:
5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 6. Same as Note 5, except the device is measured at $t \leq 10$ seconds.
 7. Same as Note 5, except the device is pulsed with $D = 0.02$ and pulse width 300 μs .
 8. Thermal resistance from junction to solder-point (at the end of the drain lead).

Thermal Characteristics

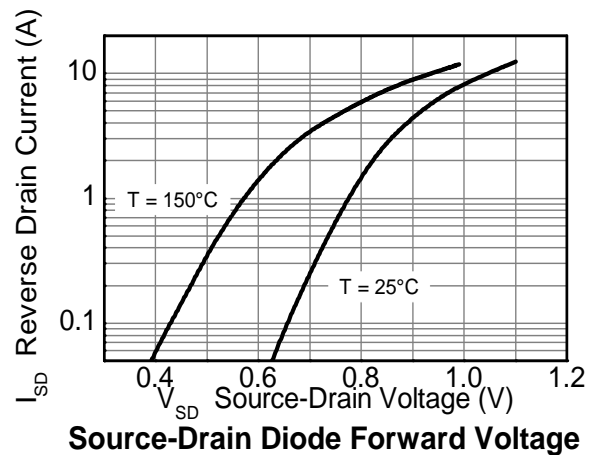
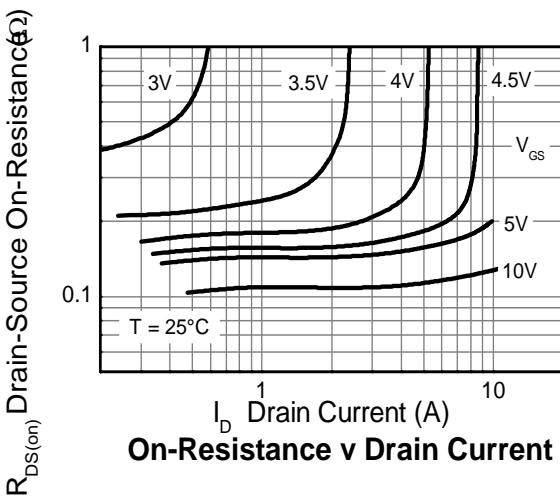
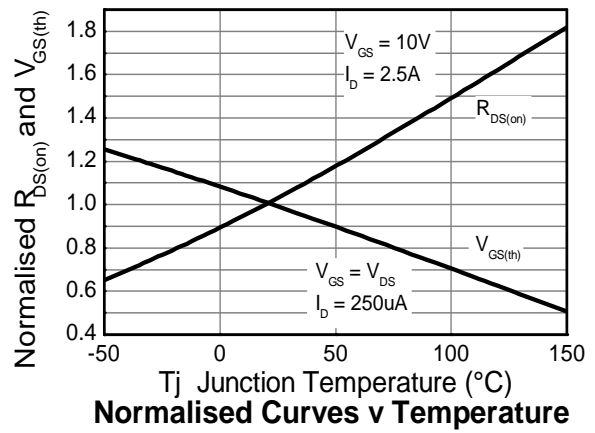
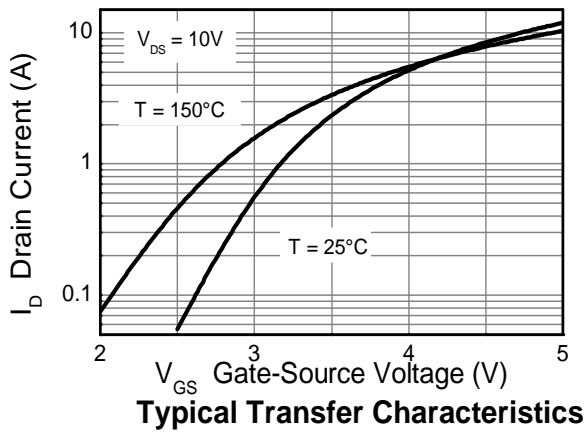
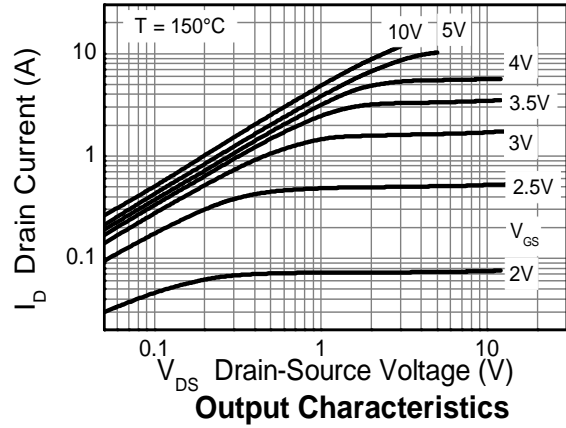
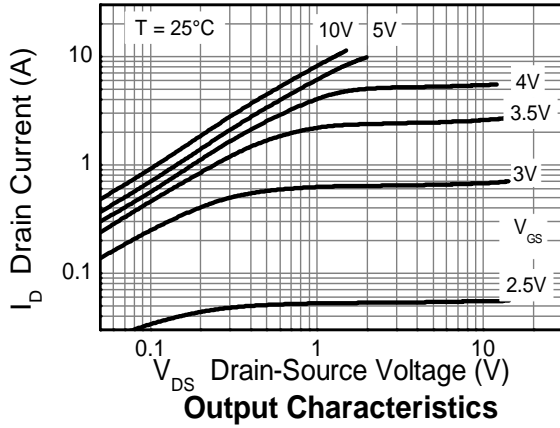


Electrical Characteristics (@ $T_A = +25^\circ\text{C}$ unless otherwise specified.)

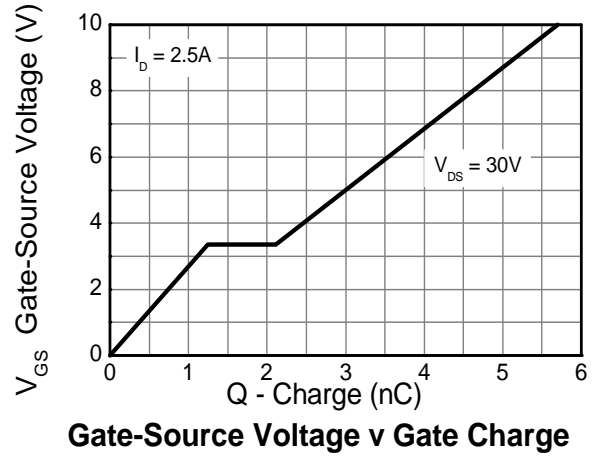
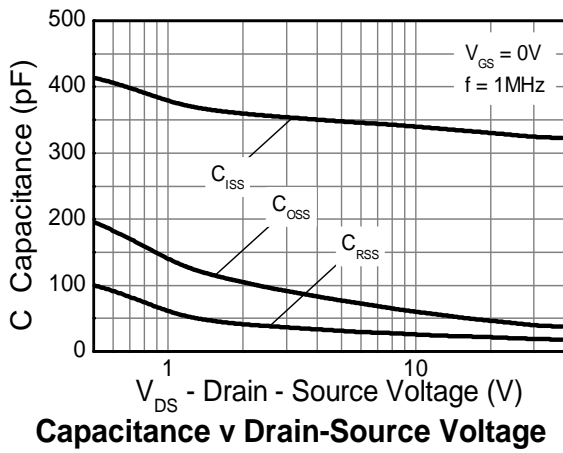
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1.0	μA	$V_{DS} = 60\text{V}$, $V_{GS} = 0\text{V}$	
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$	
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(th)}$	1.0	—	3.0	V	$I_D = 250\mu\text{A}$, $V_{DS} = V_{GS}$	
Static Drain-Source On-Resistance (Note 6)	$R_{DS(on)}$	—	0.105	0.120	Ω	$V_{GS} = 10\text{V}$, $I_D = 2.5\text{A}$	
		—	0.150	0.180		$V_{GS} = 4.5\text{V}$, $I_D = 2\text{A}$	
Forward Transconductance (Notes 6 & 7)	g_{fs}	—	4.9	—	S	$V_{DS} = 15\text{V}$, $I_D = 2.5\text{A}$	
Diode Forward Voltage (Note 6)	V_{SD}	—	0.85	0.95	V	$I_S = 2.8\text{A}$, $V_{GS} = 0\text{V}$, $T_J = +25^\circ\text{C}$	
Reverse Recovery Time (Note 7)	t_{rr}	—	21.5	—	ns	$I_S = 2.8\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$	
Reverse Recovery Charge (Note 7)	Q_{rr}	—	20.5	—	nC	$T_J = +25^\circ\text{C}$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C_{iss}	—	330	—	pF	$V_{DS} = 40\text{V}$, $V_{GS} = 0\text{V}$, $f = 1.0\text{MHz}$	
Output Capacitance	C_{oss}	—	35.2	—			
Reverse Transfer Capacitance	C_{rss}	—	17.1	—			
Gate Charge (Note 8)	Q_g	—	3.0	—	nC	$V_{GS} = 4.5\text{V}$	
Total Gate Charge (Note 8)	Q_g	—	5.7	—		$V_{GS} = 10\text{V}$	$V_{DS} = 15\text{V}$ $I_D = 2.5\text{A}$
Gate-Source Charge (Note 8)	Q_{gs}	—	1.25	—			
Gate-Drain Charge (Note 8)	Q_{gd}	—	0.86	—	ns	$V_{DD} = 30\text{V}$, $I_D = 2.5\text{A}$, $R_G = 6\Omega$, $V_{GS} = 10\text{V}$	
Turn-On Delay Time (Note 8)	$t_{D(on)}$	—	1.95	—			
Turn-On Rise Time (Note 8)	t_r	—	3.5	—			
Turn-Off Delay Time (Note 8)	$t_{D(off)}$	—	8.2	—			
Turn-Off Fall Time (Note 8)	t_f	—	4.6	—			

- Notes:
6. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.
 7. For design aid only, not subject to production testing.
 8. Switching characteristics are independent of operating junction temperature.

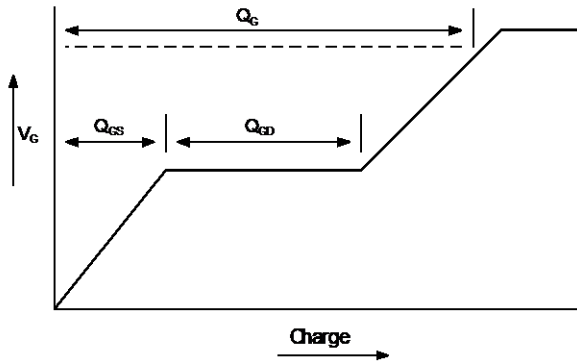
Typical Characteristics



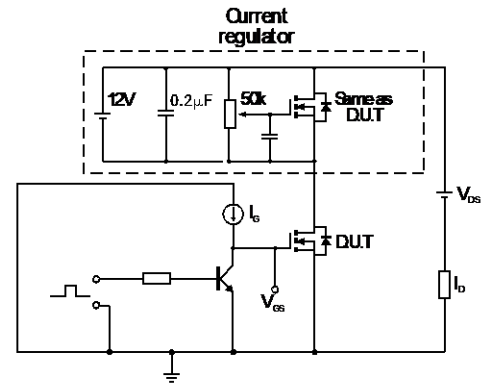
Typical Characteristics (continued)



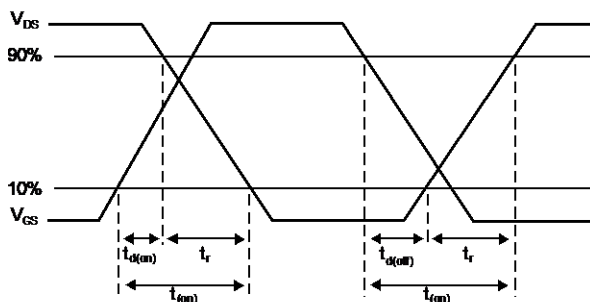
Test Circuit



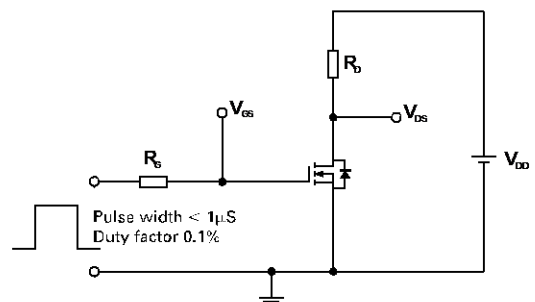
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

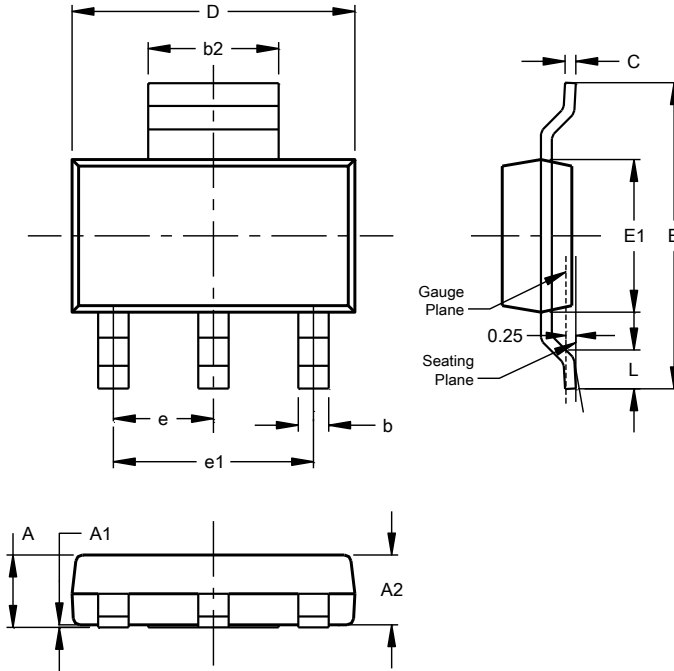


Switching time test circuit

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223 (Type DN)

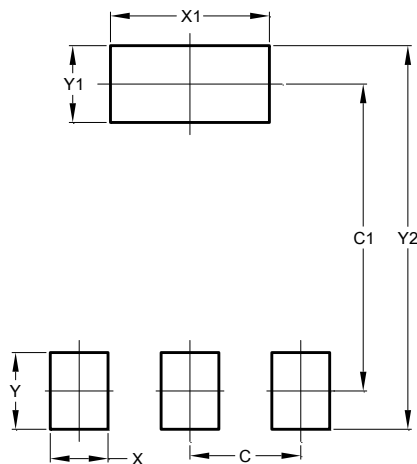


SOT223 (Type DN)			
Dim	Min	Max	Typ
A	--	1.70	--
A1	0.01	0.15	--
A2	1.50	1.68	1.60
b	0.60	0.80	0.70
b2	2.90	3.10	--
c	0.20	0.32	--
D	6.30	6.70	--
E	6.70	7.30	--
E1	3.30	3.70	--
e	--	--	2.30
e1	--	--	4.60
L	0.85	--	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223 (Type DN)



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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